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* * * * * STN Columbus * * * * *

FILE 'HOME' ENTERED AT 09:51:46 ON 22 MAY 2006

=> file uspatfull epfull pctfull
COST IN U.S. DOLLARS

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FULL ESTIMATED COST	0.21	0.21

FILE 'USPATFULL' ENTERED AT 09:52:11 ON 22 MAY 2006
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FILE 'PCTFULL' ENTERED AT 09:52:11 ON 22 MAY 2006
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=> s (silica or glass) and powder and sedimentation
L1 11555 (SILICA OR GLASS) AND POWDER AND SEDIMENTATION

=> s ((silica or glass)(w)powder) and sedimentation
L2 628 ((SILICA OR GLASS)(W) POWDER) AND SEDIMENTATION

=> dup rem L2
PROCESSING IS APPROXIMATELY 67% COMPLETE FOR L2
PROCESSING IS APPROXIMATELY 76% COMPLETE FOR L2
PROCESSING IS APPROXIMATELY 85% COMPLETE FOR L2
PROCESSING COMPLETED FOR L2
L3 628 DUP REM L2 (0 DUPLICATES REMOVED)

=> s L3 not py>1986
L4 50 L3 NOT PY>1986

=> d L4 1-25 ti

L4 ANSWER 1 OF 50 USPATFULL on STN
TI Filler for electronic element encapsulation resin and electronic element encapsulation resin composition containing the same

L4 ANSWER 2 OF 50 USPATFULL on STN
TI Heat exchange element

L4 ANSWER 3 OF 50 USPATFULL on STN
TI Shaped article and composite material and method for producing same

L4 ANSWER 4 OF 50 USPATFULL on STN
TI Abrasive, production thereof and use thereof in magnetic recording medium

L4 ANSWER 5 OF 50 USPATFULL on STN
TI Method for impregnating and embedding electrical windings

L4 ANSWER 6 OF 50 USPATFULL on STN
TI Cellular glass coated with a heat insulator

L4 ANSWER 7 OF 50 USPATFULL on STN
TI Deep dielectric isolation by fused glass

L4 ANSWER 8 OF 50 USPATFULL on STN
TI Glass composition for covering semiconductor element

L4 ANSWER 9 OF 50 USPATFULL on STN
TI Process for hydrocracking hydrocarbons with hydrotreatment-regeneration of spent catalyst

L4 ANSWER 10 OF 50 USPATFULL on STN
TI Method for forming recessed isolated regions

L4 ANSWER 11 OF 50 USPATFULL on STN
TI Method for forming a planarized integrated circuit

L4 ANSWER 12 OF 50 USPATFULL on STN
TI Method and apparatus for separating lymphocytes from anticoagulated blood

L4 ANSWER 13 OF 50 USPATFULL on STN
TI Enameled wires having resistance to overload and process for producing the same

L4 ANSWER 14 OF 50 USPATFULL on STN
TI Method of manufacturing cement products having superior mechanical strength

L4 ANSWER 15 OF 50 USPATFULL on STN
TI Production of porous gels and ceramic materials

L4 ANSWER 16 OF 50 USPATFULL on STN
TI Flowable herbicides

L4 ANSWER 17 OF 50 USPATFULL on STN
TI Acicular aluminium salts of carboxylic acids and processes for their preparation

L4 ANSWER 18 OF 50 USPATFULL on STN
TI Wall-hanging type magnetic displaying device

L4 ANSWER 19 OF 50 USPATFULL on STN
TI Surface treatment method

L4 ANSWER 20 OF 50 USPATFULL on STN
TI Coating method and article produced thereby

L4 ANSWER 21 OF 50 USPATFULL on STN
TI Cements

L4 ANSWER 22 OF 50 USPATFULL on STN
TI Filter for protection against radiation, especially with regard to direct pigmentation by solar radiation

L4 ANSWER 23 OF 50 USPATFULL on STN
TI Homogeneous, highly-filled, polyolefin composites

L4 ANSWER 24 OF 50 USPATFULL on STN
TI Primer composition and coating method using said composition

L4 ANSWER 25 OF 50 USPATFULL on STN

TI Glass for the passivation of semiconductor devices

=> d L4 8 25 ti abs bib

L4 ANSWER 8 OF 50 USPATFULL on STN

TI Glass composition for covering semiconductor element

AB A glass composition for covering a semiconductor element. The glass composition has excellent resistance to chemicals and excellent electric characteristics. The glass composition includes 3 to 8% by weight of Al.sub.2 O.sub.3, 35 to 45% by weight of SiO.sub.2, 10 to 30% by weight of ZnO, 5 to 30% by weight of PbO, 1 to 10% by weight of B.sub.2 O.sub.3, and more than 5% but not exceeding 20% by weight of an alkaline earth metal oxide selected from the group consisting of MgO, CaO, SrO and BaO, where the maximum contents of MgO, CaO, SrO and BaO are 7% by weight, 3% by weight, 7% by weight, and 15% by weight, respectively.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 85:55311 USPATFULL

TI Glass composition for covering semiconductor element

IN Furukawa, Kazuyoshi, Kawasaki, Japan

Shimbo, Masaru, Yokohama, Japan

Fukuda, Kiyoshi, Yokohama, Japan

Tanzawa, Katsujirou, Yokohama, Japan

PA Tokyo Shibaura Denki Kabushiki Kaisha, Kawasaki, Japan (non-U.S. corporation)

PI US 4542105 19850917

AI US 1982-454248 19821229 (6)

PRAI JP 1982-7930 19820121

DT Utility

FS Granted

EXNAM Primary Examiner: McCarthy, Helen M.

LREP Oblon, Fisher, Spivak, McClelland & Maier

CLMN Number of Claims: 4

ECL Exemplary Claim: 1

DRWN No Drawings

LN.CNT 520

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L4 ANSWER 25 OF 50 USPATFULL on STN

TI Glass for the passivation of semiconductor devices

AB A passivating glass for semiconductor devices. The glass contains GeO.sub.2, PbO, SiO.sub.2 and Al.sub.2 O.sub.3 and, in addition, a small defined quantity of water.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 79:25749 USPATFULL

TI Glass for the passivation of semiconductor devices

IN Trap, Hendrikus J. L., Eindhoven, Netherlands

PA U.S. Philips Corporation, New York, NY, United States (U.S. corporation)

PI US 4156250 19790522

AI US 1977-793881 19770504 (5)

PRAI NL 1976-4951 19760510

DT Utility

FS Granted

EXNAM Primary Examiner: Larkins, William D.

LREP Briody, Thomas A., Connors, Jr., Edward J., Cannon, Jr., James J.

CLMN Number of Claims: 6

ECL Exemplary Claim: 1

DRWN 1 Drawing Figure(s); 1 Drawing Page(s)

LN.CNT 207

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> d L4 25-50 ti

L4 ANSWER 25 OF 50 USPATFULL on STN
TI Glass for the passivation of semiconductor devices

L4 ANSWER 26 OF 50 USPATFULL on STN
TI Non-settling coating composition and flatting pigment

L4 ANSWER 27 OF 50 USPATFULL on STN
TI Displaying magnetic panel and its display device

L4 ANSWER 28 OF 50 USPATFULL on STN
TI Cements

L4 ANSWER 29 OF 50 USPATFULL on STN
TI Finely distributed polyvinyl chloride molding compositions capable of being sintered

L4 ANSWER 30 OF 50 USPATFULL on STN
TI Glass composition for passivating semiconductor surfaces

L4 ANSWER 31 OF 50 USPATFULL on STN
TI Highly filled polyurea foams

L4 ANSWER 32 OF 50 USPATFULL on STN
TI Inorganic-organic compositions

L4 ANSWER 33 OF 50 USPATFULL on STN
TI Filtering process using inorganic synthetically prepared filter sand

L4 ANSWER 34 OF 50 USPATFULL on STN
TI Low power high voltage thermopile

L4 ANSWER 35 OF 50 USPATFULL on STN
TI Method of making a fluorescent display device having segmentary anodes

L4 ANSWER 36 OF 50 USPATFULL on STN
TI Water glass composition

L4 ANSWER 37 OF 50 USPATFULL on STN
TI Cements comprising acrylic acid/itaconic acid copolymer and fluoroaluminosilicate **glass powder**

L4 ANSWER 38 OF 50 USPATFULL on STN
TI Construction material with calcium silicate monohydrate produced thereon in situ and composition therefor

L4 ANSWER 39 OF 50 USPATFULL on STN
TI Enamel glaze composition

L4 ANSWER 40 OF 50 USPATFULL on STN
TI Water permeability reducing inorganic coating slurry composition

L4 ANSWER 41 OF 50 USPATFULL on STN
TI LUBRICANT CONTAINING THE INORGANIC POLYMERIC GRAPHITE FLUORIDE IN AN IMPROVED DISPERSED STATE THEREOF AND METHOD FOR THE MANUFACTURE OF THE SAME

L4 ANSWER 42 OF 50 USPATFULL on STN
TI PASSIVATING METHOD

L4 ANSWER 43 OF 50 USPATFULL on STN
TI METHOD FOR MAKING MAGNETIC HEAD COMPOSED OF FERRITE

L4 ANSWER 44 OF 50 USPATFULL on STN
TI PASSIVATING SOLUTION AND METHOD

L4 ANSWER 45 OF 50 USPATFULL on STN
 TI MANUFACTURE OF BOROSILICATE **GLASS POWDER** ESSENTIALLY
 FREE OF ALKALI AND ALKALINE EARTH METALS

L4 ANSWER 46 OF 50 USPATFULL on STN
 TI ELASTOMERIC THERMOPLASTIC POLYESTER POLYURETHANE COMPOSITIONS STABILIZED
 AGAINST HYDROLYSIS

L4 ANSWER 47 OF 50 USPATFULL on STN
 TI METHOD OF COATING SOLAR CELL WITH BOROSILICATE GLASS AND RESULTANT
 PRODUCT

L4 ANSWER 48 OF 50 PCTFULL COPYRIGHT 2006 Univentio on STN
 TIEN EXPRESSION OF ENZYMATICALLY ACTIVE REVERSE TRANSCRIPTASE
 TIFR EXPRESSION D'UNE TRANSCRIPTASE INVERSE ENZYMATIQUEMENT ACTIVE

L4 ANSWER 49 OF 50 PCTFULL COPYRIGHT 2006 Univentio on STN
 TIEN A METHOD OF DETECTING OR DETERMINING HISTAMINE IN HISTAMINE CONTAINING
 MATERIALS, PARTICULARLY BODY FLUIDS AND AN ANALYTICAL MEANS FOR USE IN
 SUCH METHOD
 TIFR PROCEDE DE DETECTION OU DE DETERMINATION DE L'HISTAMINE DANS DES
 MATERIAUX CONTENANT DE L'HISTAMINE, NOTAMMENT DES FLUIDES DU CORPS ET
 MOYENS ANALYTIQUES UTILISES DANS CE PROCEDE

L4 ANSWER 50 OF 50 PCTFULL COPYRIGHT 2006 Univentio on STN
 TIEN SHAPED ARTICLE AND COMPOSITE MATERIAL AND METHOD FOR PRODUCING SAME
 TIFR ARTICLE FORME ET MATERIAU COMPOSITE ET LEUR PROCEDE DE PRODUCTION

=> d L4 45 ti abs bib

L4 ANSWER 45 OF 50 USPATFULL on STN
 TI MANUFACTURE OF BOROSILICATE **GLASS POWDER** ESSENTIALLY
 FREE OF ALKALI AND ALKALINE EARTH METALS

AB An intimate mixture of a boric oxide source compound and colloiddally
 subdivided amorphous silica is slowly heated to evolve all moisture and
 boric oxide source decomposition products. The mixture is then heated to
 a final temperature between 500° and 900° C. to form a
 borosilicate **glass powder** directly, or to form a
 borosilicate glass agglomerate which may readily be crushed to a powder.

AN 73:45348 USPATFULL
 TI MANUFACTURE OF BOROSILICATE **GLASS POWDER** ESSENTIALLY
 FREE OF ALKALI AND ALKALINE EARTH METALS

IN Iler, Ralph K., Wilmington, DE, United States
 PA E. I. du Pont de Nemours and Company, Wilmington, DE, United States
 (U.S. corporation)

PI US 3762936 19731002
 AI US 1971-112007 19710202 (5)
 RLI Continuation-in-part of Ser. No. US 1967-657042, filed on 31 Jul 1967,
 now abandoned

DT Utility
 FS Granted

EXNAM Primary Examiner: Curtis, A. B.; Assistant Examiner: Bell, Mark
 LREP Reinert; Norbert F.
 CLMN Number of Claims: 5
 DRWN No Drawings
 LN.CNT 364

=> FIL STNGUIDE

COST IN U.S. DOLLARS

SINCE FILE

TOTAL

ENTRY

SESSION

FULL ESTIMATED COST

23.47

23.68

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LOGOFF? (Y)/N/HOLD:y

COST IN U.S. DOLLARS

SINCE FILE

TOTAL

ENTRY

SESSION

FULL ESTIMATED COST

0.06

23.74

STN INTERNATIONAL LOGOFF AT 09:58:10 ON 22 MAY 2006